

The Invention Claimed Is:

1. A method of forming a portion of an integrated circuit comprising:
providing a silicon carbide base;
epitaxially growing a dielectric film on the silicon carbide base; and
forming a CMOS device on the silicon carbide base and epitaxially
5 grown dielectric film, wherein the CMOS device includes a channel region and a
gate dielectric, the channel region is formed in the silicon carbide base and the
gate dielectric is formed by the epitaxially grown dielectric film.
2. A method as defined in claim 1 wherein:
the step of epitaxially growing the dielectric film further comprises
forming a crystalline carbon-containing film on the silicon carbide base.
3. A method as defined in claim 1 wherein:
the step of epitaxially growing the dielectric film further comprises
forming a crystalline carbon film on the silicon carbide base.
4. A method as defined in claim 1 further comprising:
providing a silicon substrate; and
the step of providing the silicon carbide base further comprises
epitaxially growing the silicon carbide base on the silicon substrate.
5. A method as defined in claim 1 wherein:
the step of forming the CMOS device further comprises forming a
silicon carbide region on the epitaxially grown dielectric film, wherein the CMOS
device further includes a gate electrode formed by the silicon carbide region.
6. A method as defined in claim 5 wherein:
the step of forming the silicon carbide region on the epitaxially grown
dielectric film further comprises epitaxially growing a silicon carbide layer on the
epitaxially grown dielectric film.
7. A method as defined in claim 5 wherein:
the step of forming the silicon carbide region on the epitaxially grown

dielectric film further comprises depositing a silicon carbide layer on the epitaxially grown dielectric film.

8. A method of forming a CMOS device having a channel region and a gate dielectric region in an integrated circuit comprising:

providing a semiconductor substrate;

5 epitaxially growing a strained silicon carbide film on the semiconductor substrate;

epitaxially growing a crystalline carbon-containing film on the silicon carbide film;

forming the gate dielectric region of the CMOS device in the epitaxially grown crystalline carbon-containing film; and

10 forming the channel region of the CMOS device in the epitaxially grown strained silicon carbide film.

9. A method as defined in claim 8 wherein the CMOS device further has a gate electrode region, further comprising:

epitaxially growing a silicon carbide film on the crystalline carbon-containing film of the gate dielectric region; and

5 forming the gate electrode region of the CMOS device in the silicon carbide film epitaxially grown on the crystalline carbon-containing film of the gate dielectric region.

10. An integrated circuit comprising:

a silicon carbide base;

a dielectric film epitaxially grown on the silicon carbide base; and

5 a CMOS device including a channel region formed in the silicon carbide base and a gate dielectric formed by the epitaxially grown dielectric film.

11. An integrated circuit as defined in claim 10 wherein:

the epitaxially grown dielectric film includes crystalline carbon.

12. An integrated circuit as defined in claim 10 wherein:
the epitaxially grown dielectric film has a dielectric constant larger than 4.5.
13. An integrated circuit as defined in claim 10 further comprising:
a silicon substrate;
wherein the silicon carbide base is formed on the silicon substrate.
14. An integrated circuit as defined in claim 13 wherein:
the silicon carbide base is epitaxially grown on the silicon substrate.
15. An integrated circuit as defined in claim 14 wherein:
the epitaxially grown silicon carbide base is a strained silicon carbide film.
16. An integrated circuit as defined in claim 10 wherein:
the silicon carbide base comprises a silicon carbide substrate.
17. An integrated circuit as defined in claim 10 further comprising:
a silicon carbide region formed on the epitaxially grown dielectric film;
wherein the CMOS device further includes a gate electrode formed by the silicon carbide region.
18. An integrated circuit as defined in claim 17 wherein:
the silicon carbide region is epitaxially grown on the epitaxially grown dielectric film.
19. An integrated circuit as defined in claim 17 wherein:
the silicon carbide region is deposited on the epitaxially grown dielectric film.